Switch-mode Power Rectifiers

This series is designed for use in switching power supplies, inverters and as free wheeling diodes.

Features

- Ultrafast 25 and 50 Nanosecond Recovery Time
- 175°C Operating Junction Temperature
- Epoxy Meets UL 94 V-0 @ 0.125 in
- Low Forward Voltage
- Low Leakage Current
- Reverse Voltage to 600 V
- ESD Ratings:
 - ◆ Machine Model = C (> 400 V)
 - Human Body Model = 3B (> 16,000 V)
- SUR8 Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant*

Mechanical Characteristics:

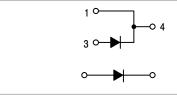
- Case: Epoxy, Molded
- Weight: 1.9 Grams (Approximately)
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperature for Soldering Purposes: 260°C Max for 10 Seconds



ON Semiconductor®

http://onsemi.com

ULTRAFAST RECTIFIERS 8.0 AMPERES, 50–600 VOLTS



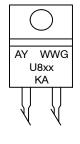




TO-220AC CASE 221B STYLE 1

TO-220 FULLPAK CASE 221AG STYLE 1

MARKING DIAGRAMS





A = Assembly Location

Y = Year WW = Work Week U8XX = Device Code

xx = 05, 10, 15, 20, 40, or 60

G = Pb-Free Package KA = Diode Polarity

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 7 of this data sheet.

^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

MAXIMUM RATINGS

		MUR/SUR8						
Rating	Symbol	805	810	815	820	840	860	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	50	100	150	200	400	600	V
Average Rectified Forward Current Total Device, (Rated V_R), $T_C = 150^{\circ}C$	I _{F(AV)}	8.0					Α	
Peak Repetitive Forward Current (Rated V _R , Square Wave, 20 kHz), T _C = 150°C	I _{FM}	16				А		
Nonrepetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz)	I _{FSM}	100		Α				
Operating Junction Temperature and Storage Temperature Range	T _J , T _{stg}	-65 to +175				°C		

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

		MUR/SUR8						
Characteristic	Symbol	805	810	815	820	840	860	Unit
Maximum Thermal Resistance, Junction-to-Case	$R_{ heta JC}$	3.0		2.0		°C/W		
Thermal Resistance, Junction-to-Case MURF860	$R_{ heta JC}$	4.75				°C/W		
Thermal Resistance, Junction-to-Ambient	$R_{ heta JA}$	73		°C/W				
Thermal Resistance, Junction-to-Ambiente MURF860	$R_{ heta JA}$	75		°C/W				

ELECTRICAL CHARACTERISTICS

		MUR/SUR8						
Characteristic	Symbol	805	810	815	820	840	860	Unit
Maximum Instantaneous Forward Voltage (Note 1) ($i_F = 8.0 \text{ A}, T_C = 150^{\circ}\text{C}$) ($i_F = 8.0 \text{ A}, T_C = 25^{\circ}\text{C}$)	VF			395 975		1.00 1.30	1.20 1.50	V
Maximum Instantaneous Reverse Current (Note 1) (Rated DC Voltage, T_J = 150°C) (Rated DC Voltage, T_J = 25°C)	İR	250 5.0		50 1	-	μΑ		
Maximum Reverse Recovery Time ($I_F = 1.0 \text{ A}, \text{ di/dt} = 50 \text{ A/µs}$) ($I_F = 0.5 \text{ A}, i_R = 1.0 \text{ A}, I_{REC} = 0.25 \text{ A}$)	t _{rr}		3	-		6 5	-	ns

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

1. Pulse Test: Pulse Width = 300 μ s, Duty Cycle \leq 2.0%.

MUR805G, MUR810G, MUR815G, MUR820G, SUR8820G

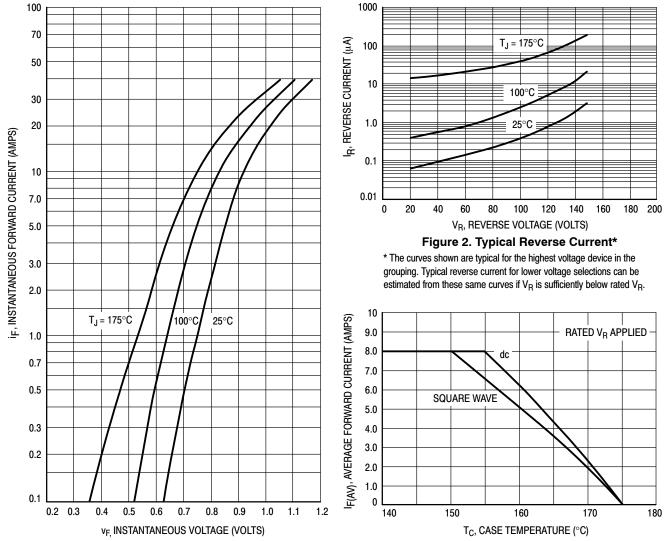


Figure 1. Typical Forward Voltage

Figure 3. Current Derating, Case

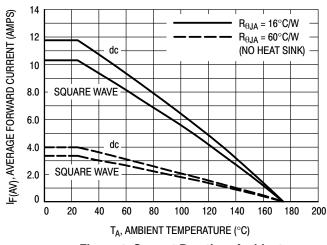


Figure 4. Current Derating, Ambient

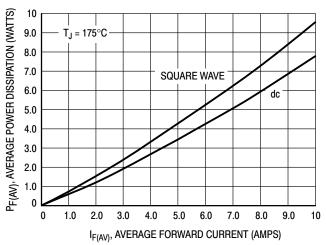


Figure 5. Power Dissipation

MUR840G, SUR8840G

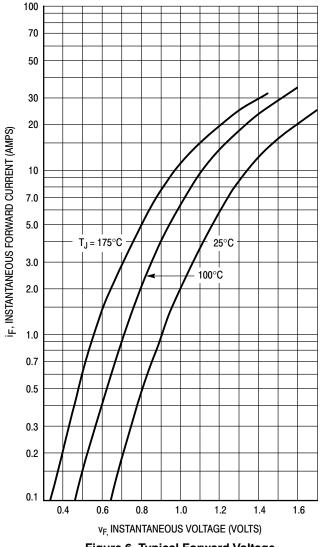


Figure 6. Typical Forward Voltage

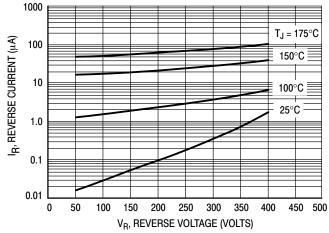


Figure 7. Typical Reverse Current*

* The curves shown are typical for the highest voltage device in the grouping. Typical reverse current for lower voltage selections can be estimated from these same curves if $V_{\rm R}$ is sufficiently below rated $V_{\rm R}$.

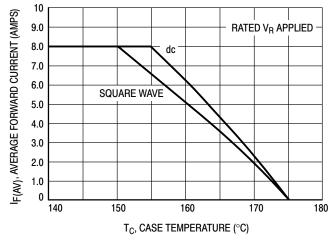


Figure 8. Current Derating, Case

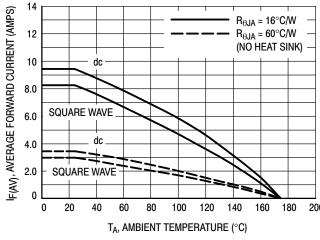


Figure 9. Current Derating, Ambient

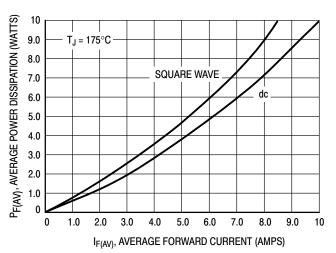


Figure 10. Power Dissipation

1000

MUR860G, MURF860G

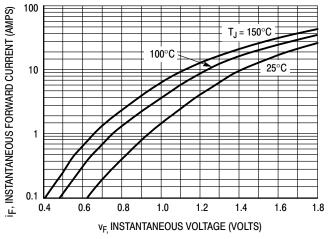
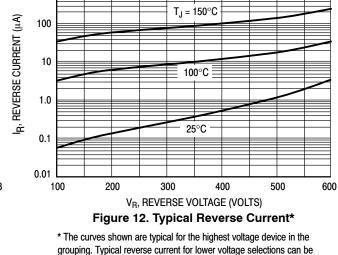


Figure 11. Typical Forward Voltage



grouping. Typical reverse current for lower voltage selections can be estimated from these same curves if V_B is sufficiently below rated V_B.

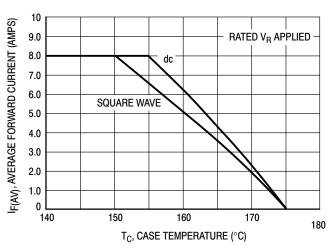


Figure 13. Current Derating, Case

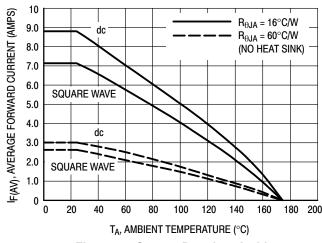


Figure 14. Current Derating, Ambient

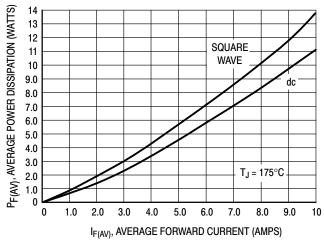


Figure 15. Power Dissipation

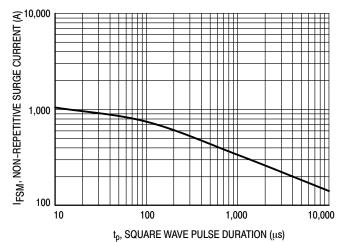


Figure 16. Typical Non-Repetitive Surge Current

^{*} Typical performance based on a limited sample size. ON Semiconductor does not guarantee ratings not listed in the Maximum Ratings table.

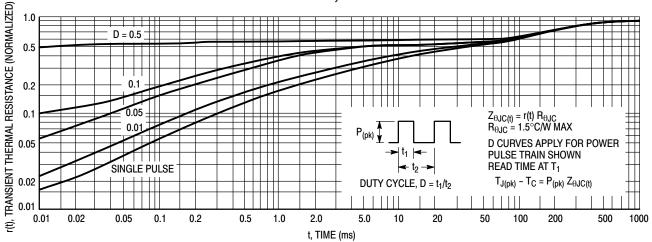


Figure 17. Thermal Response

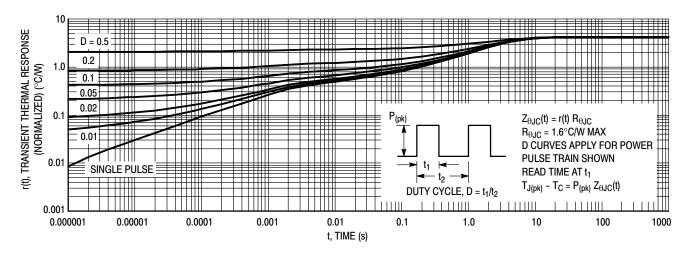


Figure 18. Thermal Response, (MURF860G) Junction-to-Case (R_{0.JC})

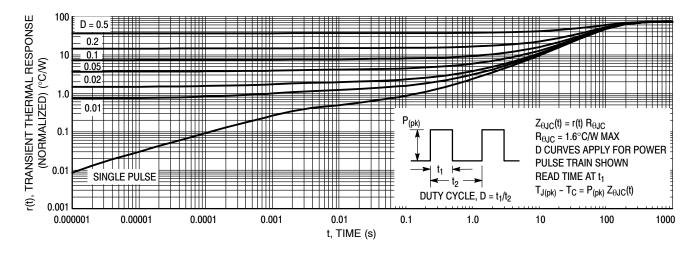


Figure 19. Thermal Response, (MURF860G) Junction-to-Ambient ($R_{\theta JA}$)

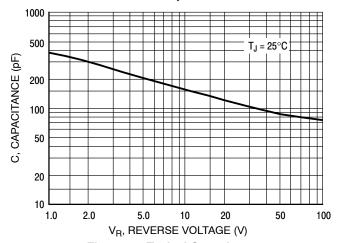


Figure 20. Typical Capacitance

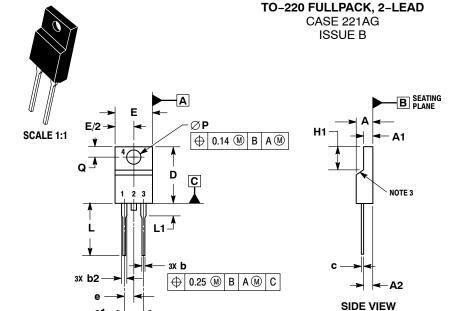
ORDERING INFORMATION

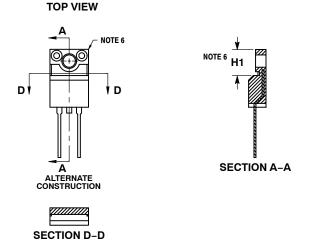
Device	Package	Shipping
MUR805G	TO-220AC (Pb-Free)	50 Units / Rail
MUR810G	TO-220AC (Pb-Free)	50 Units / Rail
MUR815G	TO-220AC (Pb-Free)	50 Units / Rail
MUR820G	TO-220AC (Pb-Free)	50 Units / Rail
SUR8820G	TO-220AC (Pb-Free)	50 Units / Rail
MUR840G	TO-220AC (Pb-Free)	50 Units / Rail
SUR8840G	TO-220AC (Pb-Free)	50 Units / Rail
MUR860G	TO-220AC (Pb-Free)	50 Units / Rail
MURF860G	TO-220FP (Pb-Free)	50 Units / Rail

DATE 27 AUG 2015



e1

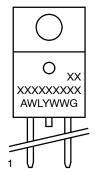




- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 2. CONTROLLING DIMENSION: MILLIMETERS.
- 3. CONTOUR UNCONTROLLED IN THIS AREA.
 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH AND GATE PROTRUSIONS. MOLD FLASH AND GATE PROTRUSIONS NOT TO EXCEED 0.13 PER SIDE. THESE DIMENSIONS ARE TO BE MEASURED AT OUTERMOST EXTREME OF THE PLASTIC BODY.
- 5. DIMENSION b2 DOES NOT INCLUDE DAMBAR PROTRUSION. LEAD WIDTH INCLUDING PROTRUSION SHALL NOT EXCEED 2.00.

SHALL NOT EXCEED 2.0							
	MILLIMETERS						
DIM	MIN	MAX					
Α	4.30	4.70					
A1	2.50	2.90					
A2	2.50	2.90					
b	0.54	0.84					
b2	1.10	1.40					
c	0.49	0.79					
D	14.22	15.88					
Е	9.65	10.67					
е	2.54	BSC					
e1	5.08	BSC					
H1	6.40	6.90					
L	12.70	14.73					
L1		2.80					
P	3.00	3.40					
Q	2.80	3.20					

GENERIC MARKING DIAGRAM*



= Assembly Location

WL = Wafer Lot

= Year

WW = Work Week

G = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

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TO-220, 2-LEAD CASE 221B-04 ISSUE F

DATE 12 APR 2013

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: INCH.

	INC	HES	MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.595	0.620	15.11	15.75
В	0.380	0.405	9.65	10.29
С	0.160	0.190	4.06	4.82
D	0.025	0.039	0.64	1.00
F	0.142	0.161	3.61	4.09
G	0.190	0.210	4.83	5.33
Н	0.110	0.130	2.79	3.30
J	0.014	0.025	0.36	0.64
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.14	1.52
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.14	1.39
T	0.235	0.255	5.97	6.48
U	0.000	0.050	0.000	1.27

Q

STYLE 1: PIN 1. CATHODE 2. N/A 3. ANODE

STYLE 2: PIN 1. ANODE 2. N/A 3. CATHODE 4. ANODE

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